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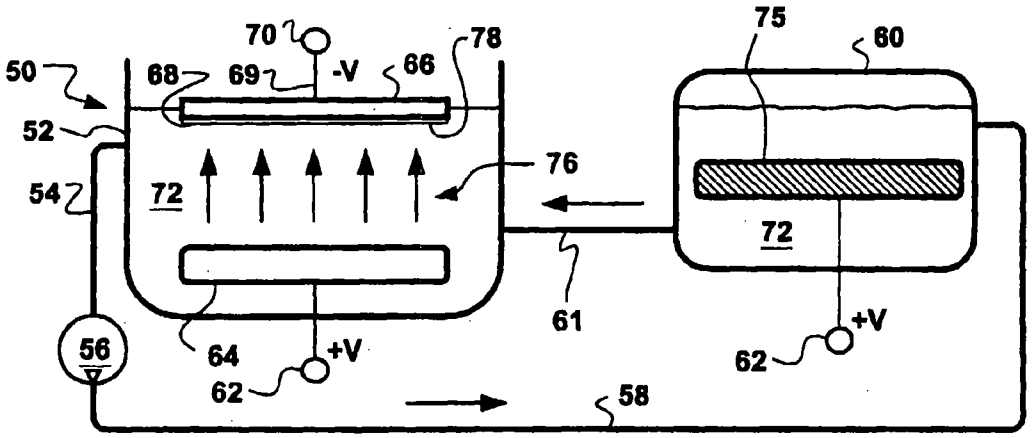
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(54) Title: PLATING SYSTEM WITH REMOTE SECONDARY ANODE FOR SEMICONDUCTOR MANUFACTURING



(57) Abstract: The present invention provides an electroplating system (50) for semiconductor wafers (66) including a plating chamber (52) connected by a circulating system (52, 56, 58) to a plating solution reservoir (60). The semiconductor wafer (66) is used as the cathode with an inert primary anode (64) in the plating chamber (52). A consumable remote secondary anode (75) in the plating solution reservoir (60) provides the metal ions for plating.

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